

ABSTRACT OF THE DISCLOSURE

9, A manufacturing method for a semiconductor device which has an element isolation region formation step; a side wall formation step; a diffusion layer formation step; an activation step; a silicide formation step; and a removing step. The element isolation region formation step forms a field oxide film on a semiconductor substrate to form an element isolation region. In order to form a diffusion layer by introducing impurities into the semiconductor substrate, after injecting a fluoride-based ion injection species into the semiconductor substrate, a thermal treatment is performed at a lower temperature than that of a subsequent thermal treatment for activating the diffusion layer so that fluorine produced from the ion injection species is discharged to the outside of the device before a siliciding step is performed.